

RAYCONN ELECTRONICS CO., LTD.

SPECIFICATION FORM

FEATURES

- ✧ 0.56 INCHES (14.20MM) DIGIT HEIGHT
- ✧ 37.60MM×19.00MM OUTLINE
- ✧ THREE DIGIT
- ✧ MONO COLOR
- ✧ EASY ASSEMBLY
- ✧ HIGH BRIGHTNESS
- ✧ SOLID STATE RELIABILITY

DESCRIPTION

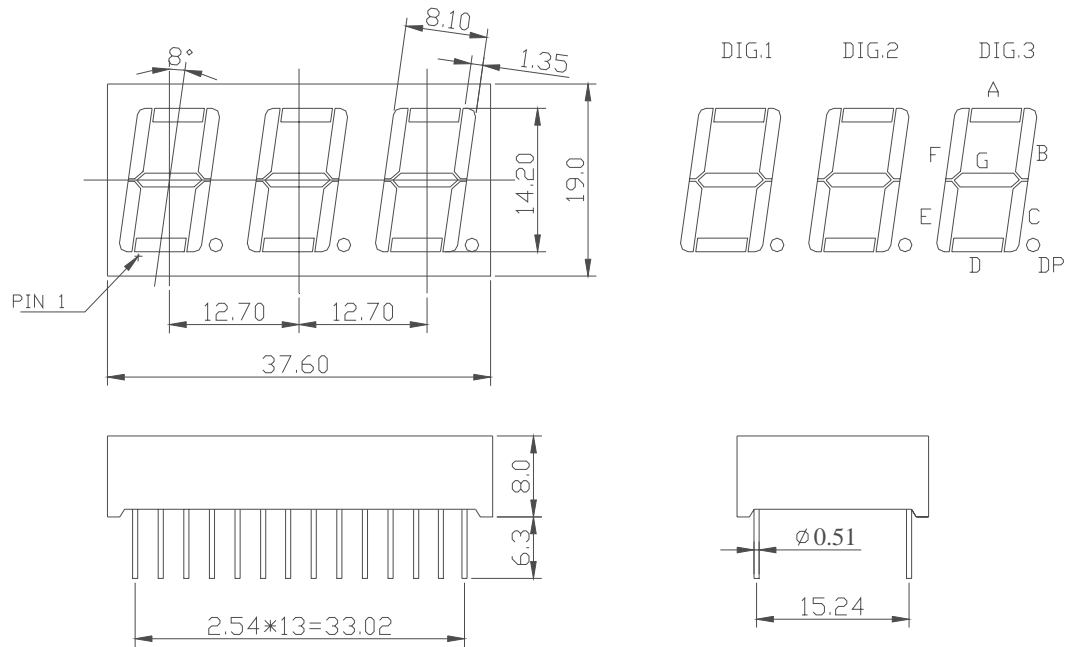
The REC-S5361ASR-3 is a 0.56 inches (14.20mm) digit height, 37.60mm×19.0mm outline, single color, three digit numeric display. This display utilizes high-red LED chips fabricated from GaAlAs epiwafer on GaAs substrate grown by liquid phase epitaxy. These devices have black face and white segments.

DEVICE

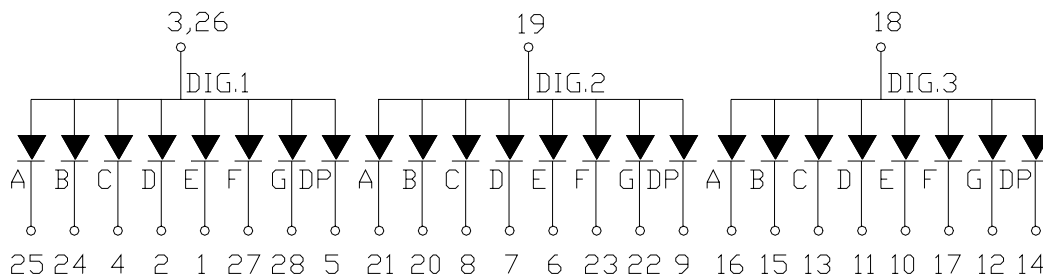
PART NO.	EMITTING COLOR	DESCRIPTION
REC-S5361ASR-3	High-Red	Common Anode

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PACKAGE DIMENSION



INTERNAL CIRCUIT DIAGRAM



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PIN CONNECTION

PIN NO.	CONNECTION	PIN NO.	CONNECTION	PIN NO.	CONNECTION
1	Cathode E Dig.1	11	Cathode D Dig.3	21	Cathode A Dig.2
2	Cathode D Dig.1	12	Cathode G Dig.3	22	Cathode G Dig.2
3	Anode Dig.1	13	Cathode C Dig.3	23	Cathode F Dig.2
4	Cathode C Dig.1	14	Cathode DP Dig.3	24	Cathode B Dig.1
5	Cathode DP Dig.1	15	Cathode B Dig.3	25	Cathode A Dig.1
6	Cathode E Dig.2	16	Cathode A Dig.3	26	Anode Dig.1
7	Cathode D Dig.2	17	Cathode F Dig.3	27	Cathode F Dig.1
8	Cathode C Dig.2	18	Anode Dig.3	28	Cathode G Dig.1
9	Cathode DP Dig.2	19	Anode Dig.2		
10	Cathode E Dig.3	20	Cathode B Dig.2		

ABSOLUTE MAXIMUM RATING AT T_A=25° C

PARAMETER	SYMBOL	MAXIMUM	UNIT
Power Dissipation per Seg.	P _{AD}	60	mW
Peak Forward Current per Seg.	I _{PF}	80	mA
Continuous Forward Current per Seg.	I _{AF}	20	mA
Reverse Voltage per Seg.	V _R	5	V
Operating Temperature Range, T _{opr}		- 25° C to + 60° C	
Storage Temperature Range, T _{stg}		- 30° C to + 85° C	
Solder Temperature : 1 / 16 inch below seating plane for 3 seconds at 260° C			

ELECTRO – OPTICAL CHARACTERISTICS AT T_A=25° C

PARAMETER	UNIT	MIN	TYPE	MAX
Luminous Intensity per Seg., I _V (I _F =20mA)	mcd	7	10	12
Peak Emission Wavelength, λ _p (I _F =20mA)	nm		640	
Special Line Half-Width, Δλ (I _F =20mA)	nm		20	
Forward Voltage per Seg., V _F (I _F =20mA)	V	1.6	1.80	2.1
Reverse Current per chipSeg., I _R , (V _R =5V)	μA			100
Luminous Intensity Matching Ratio, I _{v-m} (I _F =20mA)				2:1